Sheet 1 of

						46			31.eec <u>1</u> 0					
Form PTO-1449									ATTY DOCKET NO. 04202	APPLICATION NO. 10/512,077				
INFO		NC AN						ITATION	APPLICANT Olivier Marty	et al.				
(Use several sheets if necessary)									FILING DATE November 5, 20	GROUP				
								U.S. PATE	NT DOCUMENTS					
EXAMINER INITIAL											SUB		G DATE ROPRIATE	
	DOCUMENT NUMBER							DATE	NAME	CLASS	CLASS	ATTROTRIZE		
		┝	<u> </u>	-	<del> </del>							· ·. —	···	
				-			-							
							_				ļ			
				<u> </u>	<u>L</u>	<u> </u>			·		<u> </u>			
	<del></del>						F	OREIGN PA	TENT DOCUMENTS	<del> </del>	<del></del>			
											SUB	TRANSLATION		
	DOCUMENT NUMBER							DATE	COUNTRY	CLASS	CLASS	YES	NO	
GNK	10	2	5	8	2	7	3	3/00	EP Abstract					
GMR	2	6	8	9	9	1	2	10/93	FR w/Abstract					
	<del>                                     </del>	-		-		$\not\models$				$\overline{}$				
-/-				$\vdash$	1	$\vdash$	-			$\rightarrow$				
		<u> </u>	<u></u>	<u>0</u> ,	     THE	R		UMENTS (Inc	luding Author, Title, Date, Pertine	nt Pages, etc.)	<u></u>			
		RO	man								itv Gr	own by	,	
	GNR	Romanov et al, "GeSi Films With Reduced Dislocation Density Grown by Molecular-Beam Epitaxy on compliant Substrates Based on Porous Silicon" Applied Physics Letter, etc., Vol. 75, No. 26, Dec. 27, 1999, pp 4118-4120.												
	GNR	In MB	GaA	Jou	aAs irna	O	iant	um Well St	and Morphological C ructures on Tilted wth etc., Vol. 192,	(111) BGaAs	Grown	by	98, pp	
											$\rightarrow$			
	<u> </u>		_			_	_							
EXAMINE					9				DATE CONSIDERED	107				
EYAMINED.	Initial if circui	ion co	neidan	od 311	herhe	or er	t citat	on is in conformance	with M.P.E.P. 609; Draw line throu		onformance	and pot co	nsidered	
Include copy of										D		+00		